

Mattias Thorsell

List of Publications by Year in descending order

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docs citations

66

times ranked

790

citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of in situ NH ₃ pre-treatment of LPCVD SiN passivation on GaN HEMT performance. Semiconductor Science and Technology, 2022, 37, 035011.	2.0	8
2	High Voltage and Low Leakage GaN-on-SiC MISHEMTs on a “Buffer-Free” Heterostructure. IEEE Electron Device Letters, 2022, 43, 781-784.	3.9	9
3	Instinctual Interference-Adaptive Low-Power Receiver With Combined Feedforward and Feedback Control. IEEE Microwave and Wireless Components Letters, 2021, 31, 771-774.	3.2	4
4	Analyzing The Back-Gating Effect in GaN HEMTs with Field-Plates Using an Empirical Trap Model. , 2021, , .		0
5	Microwave Performance of “Buffer-Free”™ GaN-on-SiC High Electron Mobility Transistors. IEEE Electron Device Letters, 2020, 41, 828-831.	3.9	40
6	Impact of AlGaIn/GaN Interface and Passivation on the Robustness of Low-Noise Amplifiers. IEEE Transactions on Electron Devices, 2020, 67, 2297-2303.	3.0	6
7	Electric-Based Thermal Characterization of GaN Technologies Affected by Trapping Effects. IEEE Transactions on Electron Devices, 2020, 67, 1952-1958.	3.0	6
8	Thermal Analysis of GaN/SiC-on-Si Assemblies: Effect of Bump Pitch and Thickness of SiC Layer. , 2020, , .		0
9	Impact of Channel Thickness on the Large-Signal Performance in InAlGaIn/AlIn/GaN HEMTs With an AlGaIn Back Barrier. IEEE Transactions on Electron Devices, 2019, 66, 364-371.	3.0	33
10	Small- and Large-Signal Analyses of Different Low-Pressure-Chemical-Vapor-Deposition SiN _x Passivations for Microwave GaN HEMTs. IEEE Transactions on Electron Devices, 2018, 65, 908-914.	3.0	11
11	Accurate Modeling of GaN HEMT RF Behavior Using an Effective Trapping Potential. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 845-857.	4.6	22
12	Electron Trapping in Extended Defects in Microwave AlGaIn/GaN HEMTs With Carbon-Doped Buffers. IEEE Transactions on Electron Devices, 2018, 65, 2446-2453.	3.0	55
13	Differential Transmission Line Loop for RFID Reactive Near-Field Coupling. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 2141-2153.	4.6	3
14	Compensation of Performance Degradation due to Thermal Effects in GaN LNA Using Dynamic Bias. , 2018, , .		0
15	Compensation of Performance Degradation Due to Thermal Effects in GaN LNA Using Dynamic Bias. , 2018, , .		0
16	Optimizing the Signal-to-Noise and Distortion Ratio of a GaN LNA using Dynamic Bias. , 2018, , .		2
17	A GaN/SiC hybrid material for high-frequency and power electronics. Applied Physics Letters, 2018, 113, .	3.3	56
18	Analysis of Lateral Thermal Coupling for GaN MMIC Technologies. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 4430-4438.	4.6	1

#	ARTICLE	IF	CITATIONS
19	Analysis of thermal effects in integrated radio transmitters. , 2018, , .		0
20	Analysis of thermal effects in integrated radio transmitters. , 2018, , .		0
21	Achieving Low-Recovery Time in AlGa _N /Ga _N HEMTs With AlN Interlayer Under Low- Noise Amplifiers Operation. IEEE Electron Device Letters, 2017, 38, 926-928.	3.9	6
22	Lumped element balun with inherent complex impedance transformation. , 2017, , .		1
23	Design Equations for Lumped Element Balun With Inherent Complex Impedance Transformation. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 5162-5170.	4.6	13
24	Vector-corrected nonlinear multi-port IQ-mixer characterization using modulated signals. , 2017, , .		3
25	On the modeling of high power FET transistors. , 2016, , .		6
26	Influence on Noise Performance of Ga _N HEMTs With <i>In Situ</i> and Low-Pressure-Chemical-Vapor-Deposition SiN _x Passivation. IEEE Transactions on Electron Devices, 2016, 63, 3887-3892.	3.0	9
27	Wideband RF characterization setup with high dynamic range low frequency measurement capabilities. , 2016, , .		5
28	Carbon-Doped Ga _N on SiC Materials for Low-Memory-Effect Devices. ECS Transactions, 2016, 75, 61-65.	0.5	2
29	Shifted Source Impedance and Nonlinearity Impact on RFID Transponder Communication for Drive-Level Offsets. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 299-309.	4.6	1
30	Application Relevant Evaluation of Trapping Effects in AlGa _N /Ga _N HEMTs With Fe-Doped Buffer. IEEE Transactions on Electron Devices, 2016, 63, 326-332.	3.0	62
31	Performance Enhancement of Microwave Ga _N HEMTs Without an AlN-Exclusion Layer Using an Optimized AlGa _N /Ga _N Interface Growth Process. IEEE Transactions on Electron Devices, 2016, 63, 333-338.	3.0	17
32	Impact of Trapping Effects on the Recovery Time of Ga _N Based Low Noise Amplifiers. IEEE Microwave and Wireless Components Letters, 2016, 26, 31-33.	3.2	23
33	High frequency electromagnetic detection by nonlinear conduction modulation in graphene nanowire diodes. Applied Physics Letters, 2015, 107, .	3.3	19
34	Low-Pressure-Chemical-Vapor-Deposition SiN _x passivated AlGa _N /Ga _N HEMTs for power amplifier application. , 2015, , .		1
35	Suppression of Dispersive Effects in AlGa _N /Ga _N High-Electron-Mobility Transistors Using Bilayer SiN _x Grown by Low Pressure Chemical Vapor Deposition. IEEE Electron Device Letters, 2015, 36, 537-539.	3.9	25
36	Symmetry based nonlinear model for Ga _N HEMTs. , 2015, , .		3

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37	Evaluation of Thermal Versus Plasma-Assisted ALD Al ₂ O ₃ as Passivation for InAlN/AlN/GaN HEMTs. IEEE Electron Device Letters, 2015, 36, 235-237.	3.9	20
38	Dispersive Effects in Microwave AlGaIn/GaN HEMTs With Carbon-Doped Buffer. IEEE Transactions on Electron Devices, 2015, 62, 2162-2169.	3.0	59
39	The Effect of Forward Gate Bias Stress on the Noise Performance of Mesa Isolated GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2015, 15, 40-46.	2.0	8
40	An Oscilloscope Correction Method for Vector-Corrected RF Measurements. IEEE Transactions on Instrumentation and Measurement, 2015, 64, 2541-2547.	4.7	13
41	Symmetrical Modeling of GaN HEMTs. , 2014, , .		1
42	Symmetrical Large-Signal Modeling of Microwave Switch FETs. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 1590-1598.	4.6	15
43	Evaluation of an InAlN/AlN/GaN HEMT with Ta-based ohmic contacts and PECVD SiN passivation. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 924-927.	0.8	18
44	A Novel Technique for GaN HEMT Trap States Characterisation. , 2013, , .		6
45	A novel active load-pull system with multi-band capabilities. , 2013, , .		9
46	Investigation of Push-Pull Microwave Power Amplifiers Using an Advanced Measurement Setup. IEEE Microwave and Wireless Components Letters, 2013, 23, 220-222.	3.2	8
47	A new baseband measurement system for characterization of memory effects in nonlinear microwave devices. , 2012, , .		1
48	Noise temperature of an electronic tuner for noise parameter measurement systems. , 2012, , .		0
49	Extraction of an Electrothermal Mobility Model for AlGaIn/GaN Heterostructures. IEEE Transactions on Electron Devices, 2012, 59, 3344-3349.	3.0	9
50	Fast Multiharmonic Active Load-Pull System With Waveform Measurement Capabilities. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 149-157.	4.6	28
51	Extending the Best Linear Approximation to Characterize the Nonlinear Distortion in GaN HEMTs. IEEE Transactions on Microwave Theory and Techniques, 2011, 59, 3087-3094.	4.6	3
52	Electrothermal Access Resistance Model for GaN-Based HEMTs. IEEE Transactions on Electron Devices, 2011, 58, 466-472.	3.0	24
53	Nonlinear Characterization of Varactors for Tunable Networks by Active Source-Pull and Load-Pull. IEEE Transactions on Microwave Theory and Techniques, 2011, 59, 1753-1760.	4.6	6
54	High efficiency RF pulse width modulation with tunable load network class-E PA. , 2011, , .		3

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55	Semi-physical nonlinear circuit model with device/physical parameters for HEMTs. International Journal of Microwave and Wireless Technologies, 2011, 3, 25-33.	1.9	3
56	On the Large Signal Evaluation and Modeling of GaN FET. IEICE Transactions on Electronics, 2010, E93-C, 1225-1233.	0.6	9
57	An X-Band AlGaIn/GaN MMIC Receiver Front-End. IEEE Microwave and Wireless Components Letters, 2010, 20, 55-57.	3.2	42
58	Characterization setup for device level dynamic load modulation measurements. , 2009, , .		5
59	Thermal Study of the High-Frequency Noise in GaN HEMTs. IEEE Transactions on Microwave Theory and Techniques, 2009, 57, 19-26.	4.6	50
60	High-Efficiency LDMOS Power-Amplifier Design at 1 GHz Using an Optimized Transistor Model. IEEE Transactions on Microwave Theory and Techniques, 2009, 57, 1647-1654.	4.6	35
61	A Single-Ended Resistive X-Band AlGaIn/GaN HEMT MMIC Mixer. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 2201-2206.	4.6	25
62	An AlGaIn/GaN HEMT-Based Microstrip MMIC Process for Advanced Transceiver Design. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 1827-1833.	4.6	49
63	SiC Varactors for Dynamic Load Modulation of High Power Amplifiers. IEEE Electron Device Letters, 2008, 29, 728-730.	3.9	15
64	Characterization of the temperature dependent access resistances in AlGaIn/GaN HEMTs. , 2008, , .		3
65	Thermal characterization of the intrinsic noise parameters for AlGaIn/GaN HEMTs. , 2008, , .		6
66	A DC Comparison Study between H-Intercalated and Native Epi-Graphenes on SiC Substrates. Materials Science Forum, 0, 740-742, 129-132.	0.3	2